

# Effect of Co addition for carburizing process of Ti-oxide/SiO<sub>2</sub> into TiC/SiO<sub>2</sub>

Yasuhiro Iwama<sup>a</sup>, Nobuyuki Ichikuni<sup>a,\*</sup>, Kyoko K. Bando<sup>b</sup>, Shogo Shimazu<sup>a</sup>

<sup>a</sup> Department of Applied Chemistry and Biotechnology, Faculty of Engineering, Chiba University, Inage-ku, Chiba 263-8522, Japan

<sup>b</sup> National Institute of Advanced Industrial Science and Technology, Tsukuba, Ibaraki 305-8569, Japan

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## Abstract

Lowering the carburization temperature of Ti-oxide into TiC down to 1173 K could be achieved by the addition of Co. Co-promoted TiC/SiO<sub>2</sub> catalysts were prepared by the temperature programmed reaction (TPR) method. Co–Ti/SiO<sub>2</sub> precursors were prepared by use of the successive impregnation method (sc) and the co-impregnation method (co). Samples were characterized by X-ray absorption fine structure (XAFS) measurements and X-ray diffraction (XRD) results. The carburization degree of TiC was affected by the method of Co addition. The carburization degree of sc Co–TiC/SiO<sub>2</sub> was better than that of co Co–TiC/SiO<sub>2</sub>. The activity of thiophene hydrodesulfurization reaction at 693 K on sc Co–TiC/SiO<sub>2</sub> was higher than that on co Co–TiC/SiO<sub>2</sub>. The HDS activity was related to the carburization degree of TiC.

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## 1. Introduction

Small atoms, such as carbon or nitrogen, dissolved interstitially in the lattices of early transition metals produce a class of compounds with unique physical and chemical properties [1,2]. These interstitial compounds are referred to as early transition metal carbides (ETMC) and nitrides (ETMN). ETMC and ETMN were found to have similar activities to those of the group 8–10 metals (Pt, Pd, Rh, etc.) [3–6].

Most of works on the catalytic applications of ETMC have been focused on Mo<sub>2</sub>C and WC [7–10]. In contrast, very few works have been reported on the groups 4 and 5 metal carbides such as TiC and NbC [11–14]. The focus on Mo<sub>2</sub>C and WC has occurred in part because they could be prepared with high surface areas at moderate synthesis temperatures in the range between 900 K and 1100 K [7–10]. On the other hand, it has been reported that the carburization of bulk TiO<sub>2</sub> into TiC requires a high temperature; 1410 K [5]. Using high temperature caused a sintering of TiC, and decreased the surface area of TiC. The lowering of carburizing temperature is required for the catalytic

application of TiC. We have demonstrated that the carburizing temperature could be lowered by supporting the metal species on amorphous silica [15,16].

Co addition could be expected to promote the carburization with activating methane by dehydrogenation because it has been used for Fischer–Tropsch catalysts [17]. In this work, in order to lower carburization temperature, we added Co to TiO<sub>2</sub>, and then demonstrated carburization. In addition, Co–TiC/SiO<sub>2</sub> was prepared. For the preparation of Co–Ti/SiO<sub>2</sub>, two different methods were applied. One is successive impregnation method (sc), and the other is co-impregnation method (co). Co–Ti/SiO<sub>2</sub> precursors were carburized by using temperature programmed reaction (TPR) method. Carburization degree of Ti was characterized by using Ti K-edge XAFS (X-ray absorption fine structure) measurements. In order to investigate the effect of Co addition, Co K-edge XAFS was also measured. Thiophene HDS (hydrodesulfurization) reactions were demonstrated to investigate the relationship between the carburization degree of TiC activity and the HDS.

## 2. Experimental

Co–Ti/SiO<sub>2</sub> precursors were prepared by sc method (sc Co–Ti/SiO<sub>2</sub>) and co method (co Co–Ti/SiO<sub>2</sub>). The preparation

\* Corresponding author. Tel.: +81 43 290 3380; fax: +81 43 290 3401.

E-mail address: [ichikuni@faculty.chiba-u.jp](mailto:ichikuni@faculty.chiba-u.jp) (N. Ichikuni).

process of sc Co–Ti/SiO<sub>2</sub> consisted of two stages. First, intermediate precursors of Ti/SiO<sub>2</sub> were obtained by impregnating SiO<sub>2</sub> (Aerosil, #200) with TiCl<sub>4</sub>/HCl solutions at RT for 24 h. To decompose the titanium chloride, we calcined the intermediate precursor at 623 K in air for 2 h. Second, Co–Ti/SiO<sub>2</sub> was obtained by impregnating Ti/SiO<sub>2</sub> with aqueous cobalt chloride solution at RT for 24 h. To decompose the cobalt chloride, we calcined the precursor at 623 K in air for 2 h. Ti loading was regulated to 5 wt% with a Co/Ti molar ratio of 0.25. The co-impregnation catalyst was prepared as follows: an HCl aqueous solution of TiCl<sub>4</sub> and CoCl<sub>2</sub> was impregnated with SiO<sub>2</sub> at RT for 24 h. To decompose the titanium chloride and the cobalt chloride, we calcined the precursor at 623 K in air for 2 h (co Co–Ti/SiO<sub>2</sub>).

The Co–Ti/SiO<sub>2</sub> precursor was carburized in a 20% CH<sub>4</sub>/H<sub>2</sub> mixed gas stream to produce Co–TiC/SiO<sub>2</sub> in the TPR process. This process involves two steps: (1) raising the temperature at a linear rate of 10 K min<sup>−1</sup> to 1273 K and (2) maintaining the sample at the final temperature for a certain period.

XAFS spectra at Ti K-edge and Co K-edge were measured at RT in transmission mode at BL-10B (Co K-edges), BL-7C, 9C and 12C (Ti K-edges) using the Photon Factory in the Institute of Material Structure Science, High Energy Accelerator Research Organization (PF, IMSS-KEK) (Proposals nos. 2002G116, 2005G214). Synchrotron radiation emitted from a 2.5 GeV storage ring was monochromatized by a Si(3 1 1) channel cut monochromator or a Si(1 1 1) double crystal monochromator at BL-10B or BL-7C, 9C, 12C, respectively. Each sample was pressed into a pellet, which was 10 mm in diameter. Curve-fitting analysis of EXAFS oscillations was conducted by the EXAFS analysis program REX2000 (Rigaku Co.). Model parameters for curve-fitting analysis (back scattering amplitude and phase shift functions) were extracted from EXAFS oscillations observed for standard materials (TiO<sub>2</sub>, TiC, CoTiO<sub>3</sub>, Co foil, Co<sub>3</sub>O<sub>4</sub> and CoS), or they were created by FEFF.

The XRD (X-ray diffraction) analysis (Bruker axs, MXP3) was also carried out. HDS of thiophene was performed in continuous flow system interfaced to a gas chromatograph (SHIMADZU, GC-8A) with a TCD detector. The main products were 1-butene and 2-butene. The catalyst (0.4 g) was pretreated under H<sub>2</sub> flow (10 ml min<sup>−1</sup>) for 0.5 h at 1073 K or 773 K, prior to use. HDS reaction was monitored under 2.8% thiophene/H<sub>2</sub> (5 ml min<sup>−1</sup>) at 693 K.

### 3. Results and discussion

#### 3.1. Carburization of bulk TiO<sub>2</sub>

XRD patterns of TiO<sub>2</sub>, TiC, carburized TiO<sub>2</sub> and carburized Co–TiO<sub>2</sub> are shown in Fig. 1. In the case of carburized TiO<sub>2</sub>, the Ti<sub>3</sub>O<sub>5</sub> phase was observed and no peak attributed to TiC was appeared. On the other hand, the patterns for carburized Co–TiO<sub>2</sub> showed TiC phase clearly. Such results mean that TiO<sub>2</sub> was not carburized at 1273 K without Co additive, but was carburized to produce TiC with Co additive. In the case of carburized Co–TiO<sub>2</sub>, Co metal phase was observed as well as

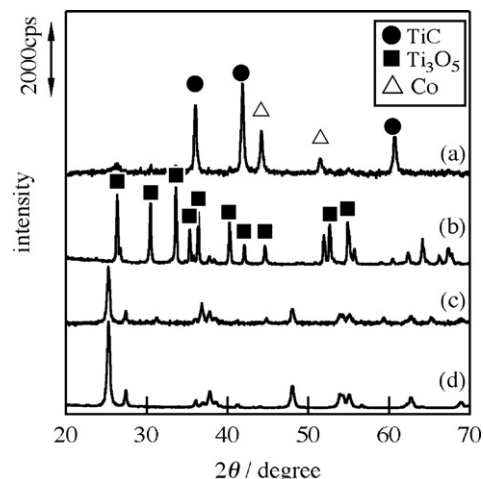


Fig. 1. XRD patterns of (a) carburized Co–TiO<sub>2</sub>, (b) carburized TiO<sub>2</sub>, (c) Co–TiO<sub>2</sub> and (d) bulk TiO<sub>2</sub>.

TiC phase. It was found that Co oxide was reduced to Co metal during the carburization. We supposed that the carburization of TiO<sub>2</sub> proceeded focusing around reduced Co.

In order to optimize the carburization condition, we prepared carburized Co–TiO<sub>2</sub> by controlling the carburization temperature and the retention time. Fig. 2 shows XRD patterns of carburized Co–TiO<sub>2</sub> as a function of carburization temperature (1273 K, 1223 K, 1173 K and 1073 K). The XRD pattern of Co–TiO<sub>2</sub> carburized at 1073 K shows only Ti<sub>3</sub>O<sub>5</sub> phase. It can be said that TiC was not formed by a carburization temperature as low as 1073 K. In the case of Co–TiO<sub>2</sub> carburized at 1173 K, however, TiC phase was observed slightly besides the main Ti<sub>3</sub>O<sub>5</sub> phase. It was found that TiC was formed by the carburization above 1173 K. In other words, the carburization temperature of Ti-oxide into TiC could be lowered down to 1173 K by addition of Co. In the case of Co–TiO<sub>2</sub> carburized at 1223 K, the TiC phase was larger compared to the case of Co–TiO<sub>2</sub> carburized at 1173 K. Raising the carburization temperature up to 1273 K, we could distinctly observed the TiC phase

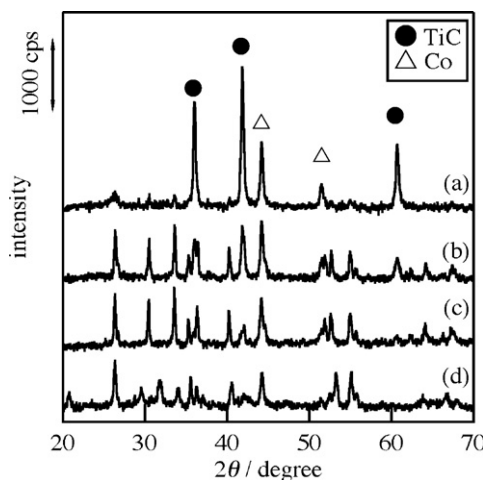


Fig. 2. XRD patterns of carburized Co–TiO<sub>2</sub> varied with the carburization temperature: (a) 1273 K, (b) 1223 K, (c) 1173 K and (d) 1073 K.

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